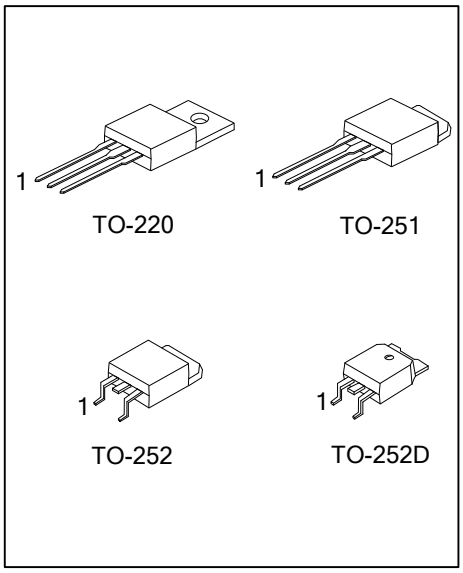
UTT30N06

Power MOSFET

30A, 60V N-CHANNEL POWER MOSFET



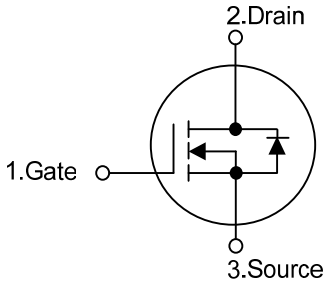
■ DESCRIPTION

The UTC **UTT30N06** is a low voltage power MOSFET and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and excellent avalanche characteristics. This power MOSFET is usually used in automotive applications of power supplies, high efficient DC to DC converters and battery operated products.

■ FEATURES

* $R_{DS(ON)}$ < 40mΩ @ V_{GS} = 10 V, I_D = 15 A
* Low reverse transfer Capacitance (C_{RSS} = typical 80 pF)
* Fast switching capability
* Avalanche energy specified
* Improved dv/dt capability

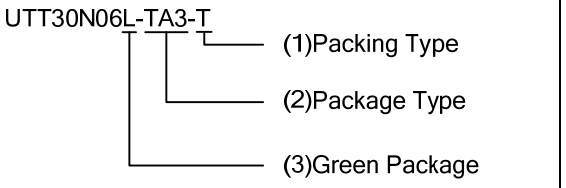
■ SYMBOL



■ ORDERING INFORMATION

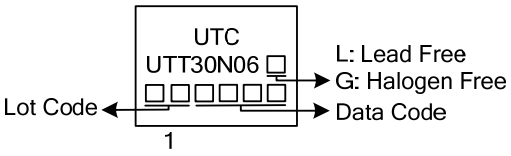
Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
UTT30N06L-TA3-T	UTT30N06G-TA3-T	TO-220	G	D	S	Tube
UTT30N06L-TM3-T	UTT30N06G-TM3-T	TO-251	G	D	S	Tube
UTT30N06L-TN3-R	UTT30N06G-TN3-R	TO-252	G	D	S	Tape Reel
UTT30N06L-TND-R	UTT30N06G-TND-R	TO-252D	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source



(1) T: Tube, R: Tape Reel
(2) TA3: TO-220, TM3: TO-251, TN3: TO-252, TND: TO-252D
(3) L: Lead Free, G: Halogen Free and Lead Free

■ MARKING



■ ABSOLUTE MAXIMUM RATINGS (T_C=25°C, unless otherwise specified)

PARAMETER			SYMBOL	RATINGS	UNIT
Drain-Source Voltage			V_{DSS}	60	V
Gate-Source Voltage			V_{GSS}	±20	V
Drain Current	Continuous	T_C = 25°C	I_D	30	A
		T_C = 100°C		21.3	A
	Pulsed (Note 1)		I_{DM}	120	A
Avalanche Energy	Single Pulsed (Note 2)		E_{AS}	45	mJ
Peak Diode Recovery dv/dt (Note 3)			dv/dt	7.5	V/ns
Power Dissipation	TO-220		P_D	89	W
	TO-251/TO-252/TO-252D			44	
Junction Temperature			T_J	+150	°C
Operation Temperature			T_{OPR}	-55 ~ +150	°C
Storage Temperature			T_{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. Repeativity rating: pulse width limited by junction temperature
3. L=0.1mH, I_{AS}=30A, V_{DD}=25V, R_G=20Ω, Starting T_J=25°C
4. I_{SD}≤50A, di/dt≤300A/μs, V_{DD}≤BV_{DSS}, Starting T_J=25°C

■ THERMAL DATA

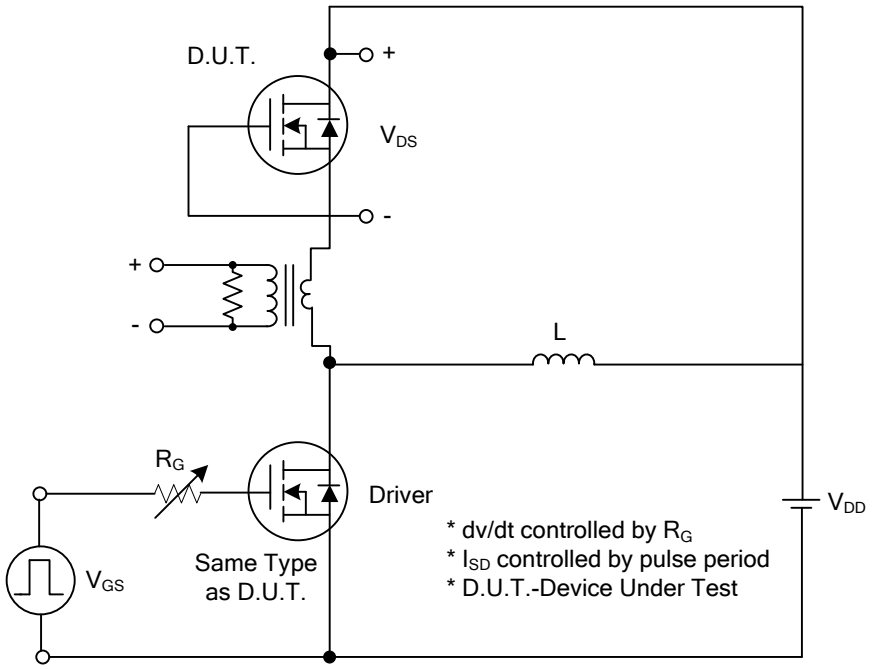
PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient	TO-220	θ_{JA}	62	°C/W
	TO-251/TO-252/TO-252D		110	
Junction to Case	TO-220	θ_{JC}	1.4	°C/W
	TO-251/TO-252/TO-252D		2.85	

■ ELECTRICAL CHARACTERISTICS (T_C=25°C, unless otherwise specified)

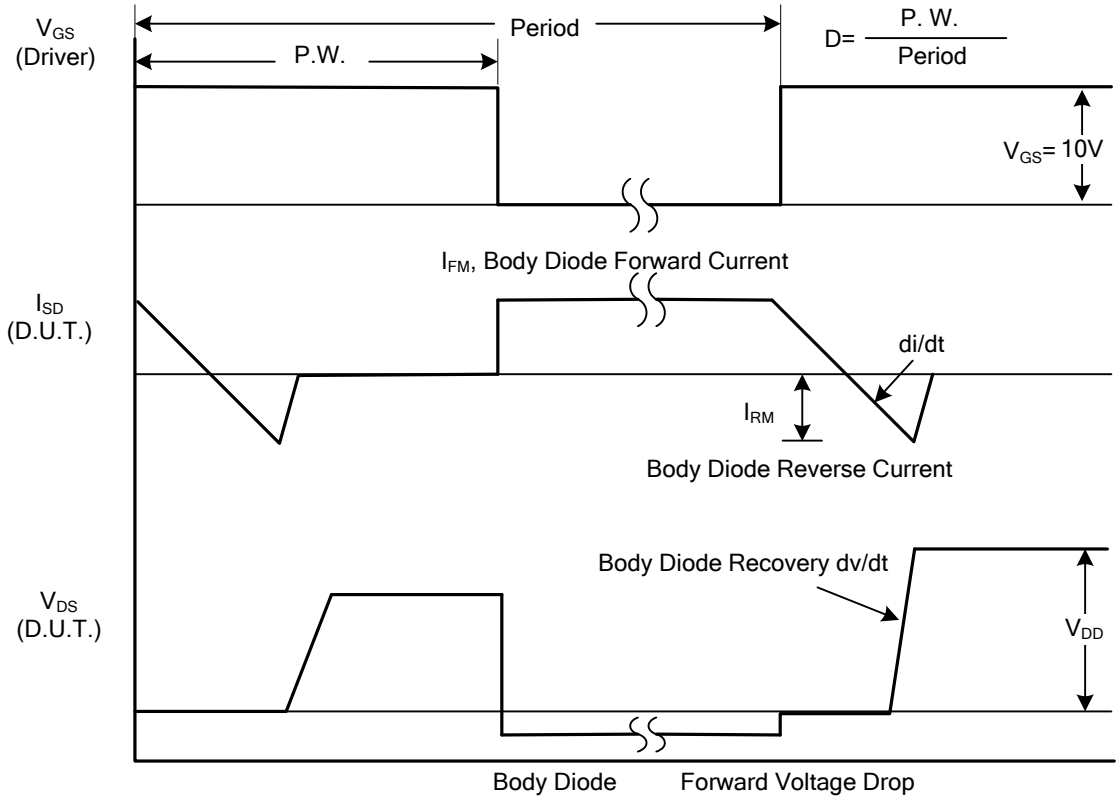
PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV_{DSS}	V_{GS} = 0 V, I_D = 250 μA	60			V
Drain-Source Leakage Current		I_{DSS}	V_{DS} = 60 V, V_{GS} = 0 V			10	μA
Gate-Source Leakage Current	Forward	I_{GSS}	V_{GS} = 20V, V_{DS} = 0 V			100	nA
	Reverse		V_{GS} = -20V, V_{DS} = 0 V			-100	nA
Breakdown Voltage Temperature Coefficient		$\triangle BV_{DSS}/\triangle T_J$	I_D=250μA,Referenced to 25℃		0.06		V/℃
ON CHARACTERISTICS							
Gate Threshold Voltage		$V_{GS(TH)}$	V_{DS} = V_{GS}, I_D = 250μA	1.0		3.0	V
Static Drain-Source On-State Resistance		$R_{DS(ON)}$	V_{GS} = 10 V, I_D = 15 A		32	40	mΩ
DYNAMIC CHARACTERISTICS							
Input Capacitance		C_{ISS}	V_{GS} = 0 V, V_{DS} = 25 V, f = 1MHz		800	1000	pF
Output Capacitance		C_{OSS}			130	200	pF
Reverse Transfer Capacitance		C_{RSS}			80	100	pF
SWITCHING CHARACTERISTICS							
Total Gate Charge		Q_G	V_{DS} = 60V, V_{GS} = 10 V, I_D = 24A (Note 1, 2)		80	100	nC
Gate-Source Charge		Q_{GS}			15		nC
Gate-Drain Charge		Q_{GD}			50		nC
Turn-On Delay Time		$t_{D(ON)}$	V_{DD} = 30V, I_D =1.0 A, V_{GS}=10V (Note 1, 2)		35	70	ns
Turn-On Rise Time		t_R			40	80	ns
Turn-Off Delay Time		$t_{D(OFF)}$			220	280	ns
Turn-Off Fall Time		t_F			100	120	ns
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS							
Maximum Continuous Drain-Source Diode Forward Current		I_S				30	A
Maximum Pulsed Drain-Source Diode Forward Current		I_{SM}				120	A
Drain-Source Diode Forward Voltage		V_{SD}	V_{GS} = 0 V, I_S = 30A			1.4	V
Reverse Recovery Time		t_{rr}	V_{GS} = 0 V, I_S = 30A, dI_F / dt = 100 A/μs (Note 1)		40		ns
Reverse Recovery Charge		Q_{rr}			70		μC

Notes: 1. Pulse Test : Pulse width ≤300μs, Duty cycle ≤ 2%
2. Essentially independent of operating temperature

■ TEST CIRCUITS AND WAVEFORMS

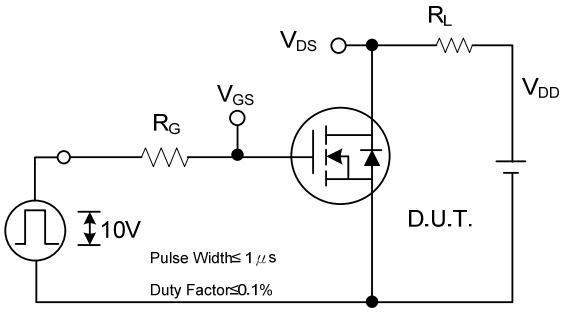


Peak Diode Recovery dv/dt Test Circuit

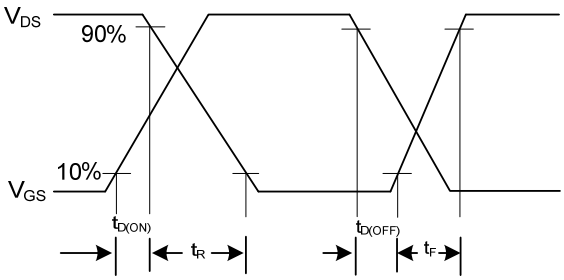


Peak Diode Recovery dv/dt Waveforms

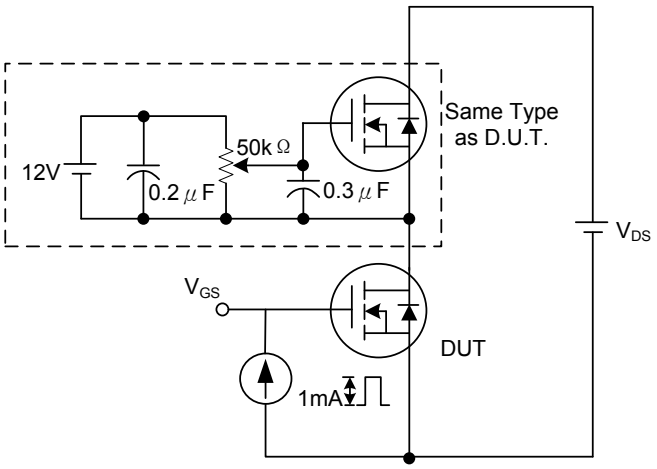
■ TEST CIRCUITS AND WAVEFORMS (Cont.)



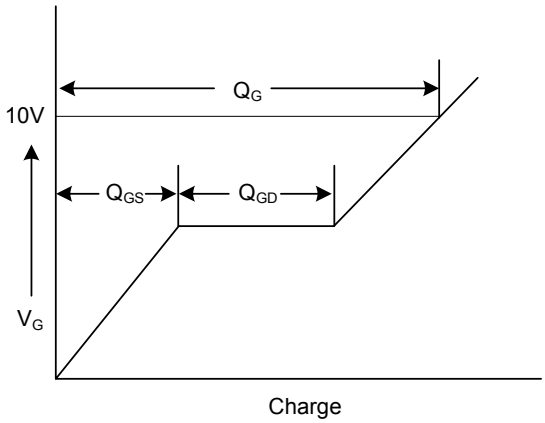
Switching Test Circuit



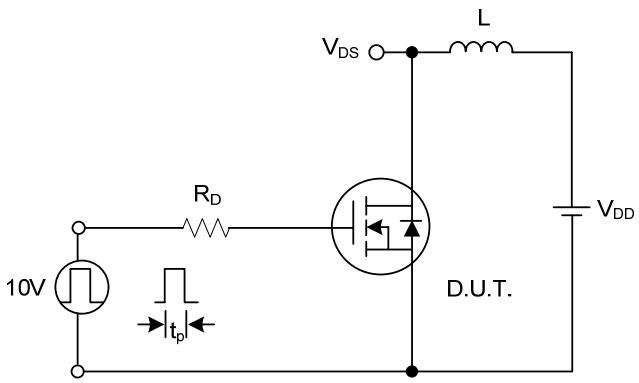
Switching Waveforms



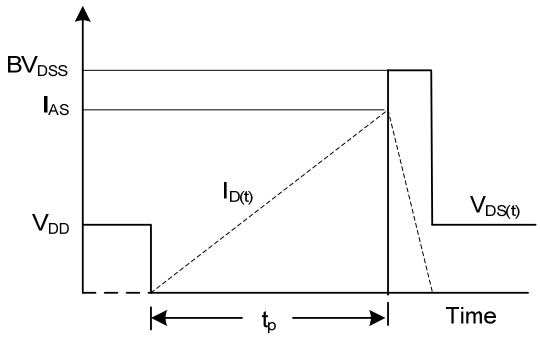
Gate Charge Test Circuit



Gate Charge Waveform



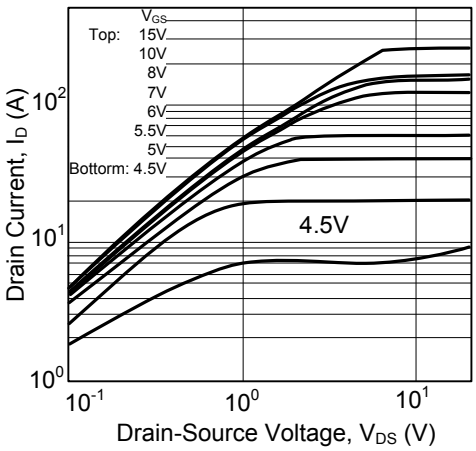
Unclamped Inductive Switching Test Circuit



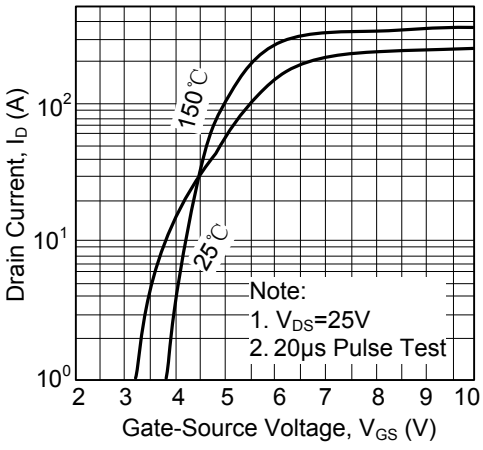
Unclamped Inductive Switching Waveforms

■ TYPICAL CHARACTERISTICS

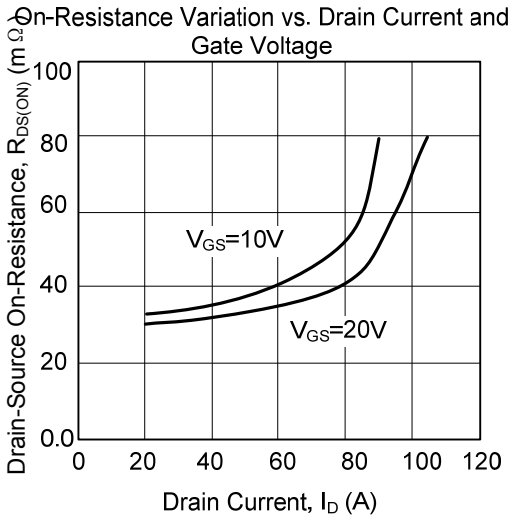
On-State Characteristics



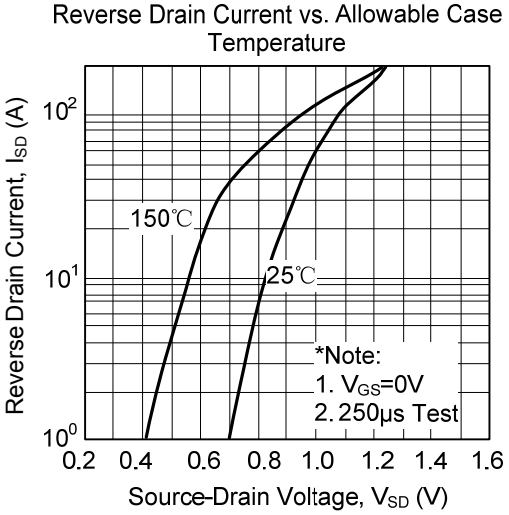
Transfer Characteristics



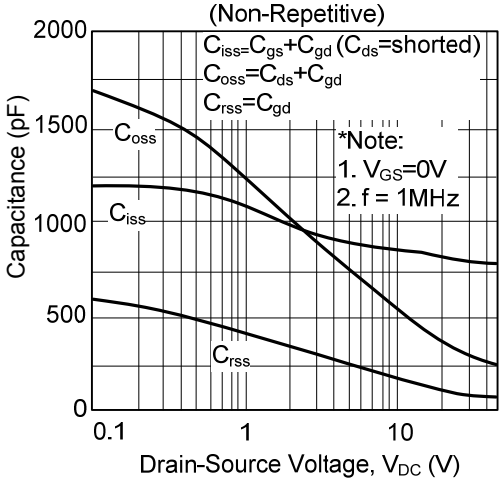
On-Resistance Variation vs. Drain Current and Gate Voltage



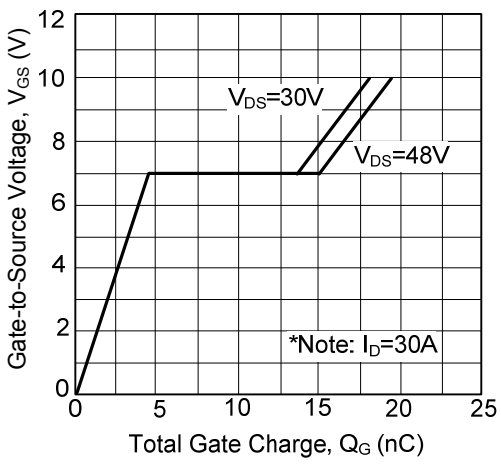
Reverse Drain Current vs. Allowable Case Temperature



Capacitance Characteristics (Non-Repetitive)

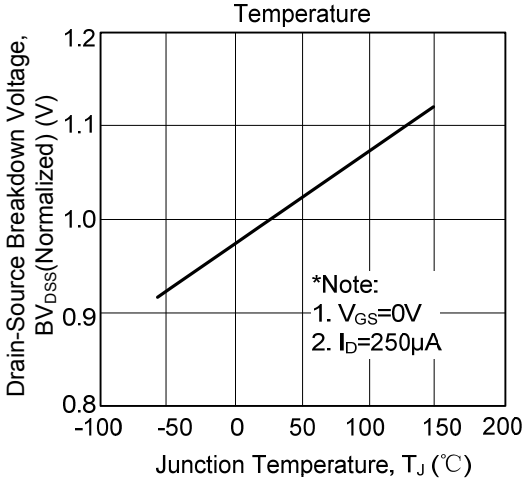


Gate Charge Characteristics

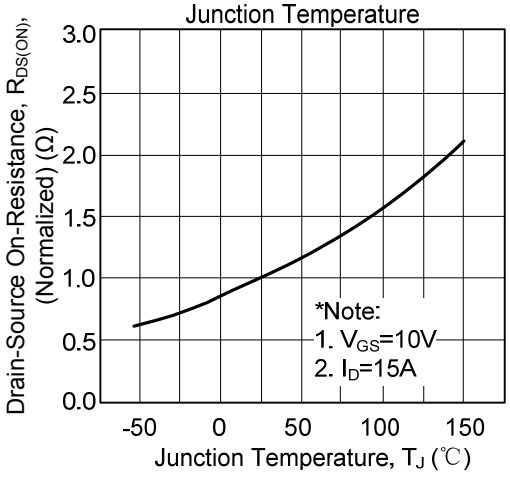


■ TYPICAL CHARACTERISTICS(Cont.)

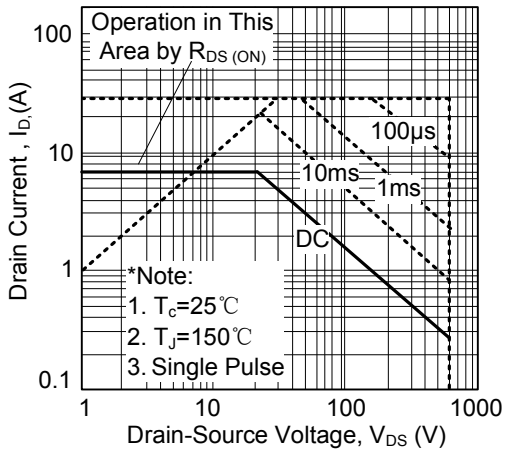
Breakdown Voltage Variation vs. Junction Temperature



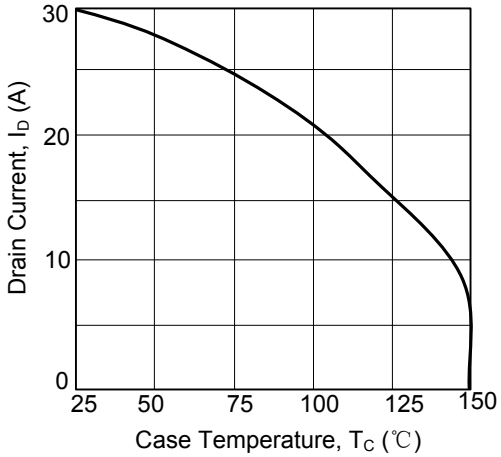
On-Resistance Variation vs. Junction Temperature



Maximum Safe Operating



Maximum Drain Current vs. Case Temperature



Transient Thermal Response Curve